



PATENT
Attorney Docket No. CIS-001CP

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Schowalter and Slack
SERIAL NO.: 10/ 822,336 **GROUP NO.:** 1722
FILING DATE: April 12, 2004 **EXAMINER:** Kunemund, R.
TITLE: Powder Metallurgy Crucible For Aluminum Nitride Crystal Growth

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. References A11 and B1 were previously cited in U.S. Patent Application Serial No. 09/251,106, from which this application claims priority. Accordingly, pursuant to 37 C.F.R. § 1.98(d), Applicants have not supplied copies of those references, but shall do so upon request.

Also, in accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98(a)(2), Applicants have not supplied copies of the U.S. patents and publications cited in the attached Form PTO-1449, but shall do so upon request. Copies of the foreign patent documents B2 and non-patent publications C1-C7 are enclosed.

Information Disclosure Statement

Serial No. 10/822,336

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REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or

(2) after the period defined in (1) but before the mailing date of a **final action or a notice of allowance** under 37 C.F.R. 1.311, and

the requisite Statement is below, **OR**

the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or

(3) after the mailing date of a **final action or notice of allowance** but before the payment of the **issue fee**, **AND**

the requisite Statement is below, **AND**

the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

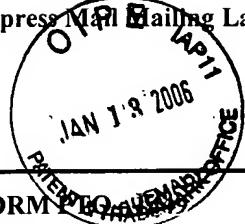
Respectfully submitted,



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FORM 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		ATTORNEY DOCKET NO.: CIS-001CP APPLICANTS: Schowalter and Slack SERIAL NO.: 10/822,336 FILING DATE: April 12, 2004 GROUP: 1722		
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U.S. PATENT DOCUMENTS

EXAM INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A1	4,234,554	11/18/80	Rabenau <i>et al.</i>			
	A2	5,858,085	01/12/1999	Arai <i>et al.</i>			
	A3	5,858,086	01/12/1999	Hunter			
	A4	5,909,036	06/01/1999	Tanaka <i>et al.</i>			
	A5	5,972,109	10/26/1999	Hunter			
	A6	6,001,748	06/04/1997	Tanaka <i>et al.</i>			
	A7	6,045,612	04/04/2000	Hunter			
	A8	6,048,813	04/11/2000	Hunter			
	A9	6,063,185	05/16/2000	Hunter			
	A10	6,086,672	07/11/2000	Hunter			
	A11	6,187,089	02/13/2001	Phillips <i>et al.</i>			
	A11	6,296,956	10/02/2001	Hunter			

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B1	2000-154090	06/2000	JP				YES	N
	B2	02 018379A	01/22/1990	JP				YES	N

EXAMINER

DATE CONSIDERED

FORM PTO - 1449		ATTORNEY DOCKET NO.: CIS-001CP
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		APPLICANTS: Schowalter and Slack
		SERIAL NO.: 10/822,336
		FILING DATE: April 12, 2004
		GROUP: 1722
OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
	C1	Dryburgh, "Estimation of maximum growth rate for aluminum nitride crystals by direct sublimation", <i>J. Crystal Growth</i> 125, 65-68 (1992).
	C2	A.S. Segal S. Yu, Karpov, Yu. N. Makarov, E.N. Mokhov, A.D. Roenkov, M.G. Ramm, Yu. A. Vodakov, "On mechanisms of sublimination growth of AlN bulk crystals", <i>J. Crystal Growth</i> 211, 68-72 (2000).
	C3	B. Raghorthamachar, W.M. Vetter, M. Dudley, R. Dalmau, R. Schlesser, Z. Sitar, E. Michaels, and J.W. Kolis, "Synchrotron white beam topography characterization of physical vapor transport grown AlN and ammonothermal GaN", <i>J. Crystal Growth</i> 246, 271-280 (2002).
	C4	R. Schlesser, R. Dalmau, and Z. Sitar, "Seeded growth of AlN bulk single crystals by sublimation", <i>J. Crystal Growth</i> 241, 416-420 (2002).
	C5	L.J. Schowalter, G.A. Slack, J.B. Whitlock, K. Morgan, S.B. Schujman, B. Raghorthamachar, M. Dudley, and K.R. Evans, "Fabrication of native, single-crystal AlN substrates", <i>Phys. Stat. Sol. (c)</i> , 104, (2003).
	C6	V. Noveksi, R. Schlesser, S. Mahajan, S. Beaudoin, and Z. Sitar, "Growth of AlN crystals on AlN/SiC seeds by AlN powder sublimation in nitrogen atmosphere", <i>MRS Internet J. Nitride Semicond. Res.</i> 9, 2 (2004).
	C7	V. Noveksi, R. Schlesser, S. Mahajan, S. Beaudoin, and Z. Sitar, "Mass transfer in AlN crystal growth at high temperatures", <i>J. Crystal Growth</i> 264, 369-378 (2004).
EXAMINER		DATE CONSIDERED

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